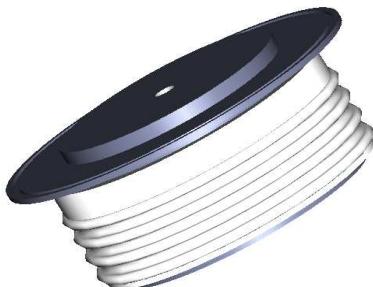


# GPDN6076


**RECTIFIER DIODE**

**BLOCKING VOLTAGE UP TO** 6000 V  
**AVERAGE CURRENT** 765 A  
**SURGE CURRENT** 11 kA

**BLOCKING CHARACTERISTICS**

Characteristic	Conditions	Value
V <sub>RRM</sub>	Repetitive peak reverse voltage	6000 V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage	6100 V
I <sub>RRM</sub>	Repetitive peak reverse current, max.	50 mA

**FORWARD CHARACTERISTICS**

I <sub>F(AV)</sub>	Average forward current	Sine wave, 180° conduction, T <sub>h</sub> = 55°C	765 A
I <sub>F(RMS)</sub>	R.M.S. forward current	Sine wave, 180° conduction, Th = 55°C	1202 A
I <sub>FSM</sub>	Surge forward current	Non rep. half sine wave, 50 Hz, V <sub>R</sub> = 0 V, T <sub>j</sub> = T <sub>jmax</sub>	11 kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination		605 kA <sup>2</sup> s
V <sub>F(TO)</sub>	Threshold voltage	T <sub>j</sub> = T <sub>jmax</sub>	1.066 V
r <sub>F</sub>	Forward slope resistance	T <sub>j</sub> = T <sub>jmax</sub>	0.778 mΩ
V <sub>FM</sub>	Peak forward voltage, max	Forward current I <sub>F</sub> = 800 A, T <sub>j</sub> = T <sub>jmax</sub>	1.69 V

**SWITCHING CHARACTERISTICS**

Q <sub>rr</sub>	R <sub>reverse recovery charge, typ</sub>	T <sub>j</sub> = T <sub>jmax</sub> , I <sub>F</sub> = A, dI/dt = A/μs	μC
I <sub>rr</sub>	Reverse recovery current		A

**THERMAL AND MECHANICAL CHARACTERISTICS**

R <sub>th(j-c)</sub>	Thermal resistance (junction to case)	Double side cooled	0.042 °C/W
R <sub>th(c-h)</sub>	Thermal resistance (case to heatsink)	Double side cooled	0.007 °C/W
T <sub>jmax</sub>	Max operating junction temperature		150 °C
T <sub>stg</sub>	Storage temperature		-40 / 150 °C
F	Clamping force ± 10%		11 kN
	Mass		300 g